



1N5819

Surface Mount Schottky Barrier Diodes

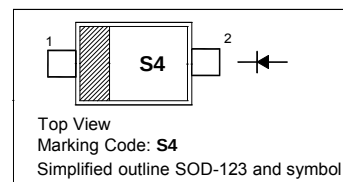
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Features

- Low Forward Voltage

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
		30	
		20	
Reverse Voltage	V_R	40	V
		30	
		20	
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	I_{FSM}	2	A
Power Dissipation	P_{tot}	400	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	40	-	-	V
		30	-	-	
		20	-	-	
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$	I_R	-	-	5	μA
		-	-	5	
		-	-	5	
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	-	-	0.37	V
		-	-	0.6	
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	10	-	ns

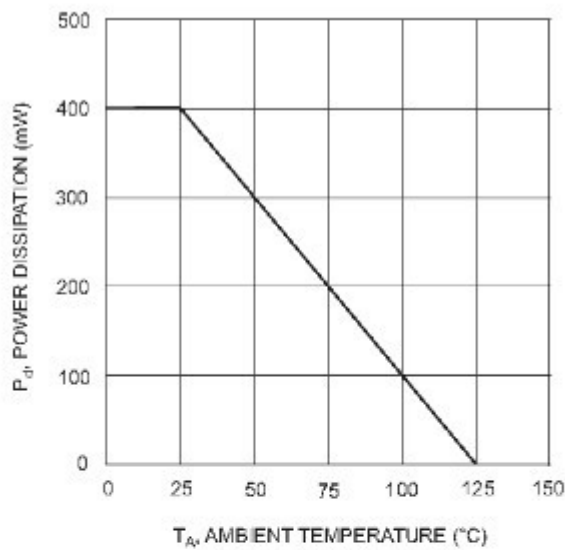


Fig. 1 Power Derating Curve

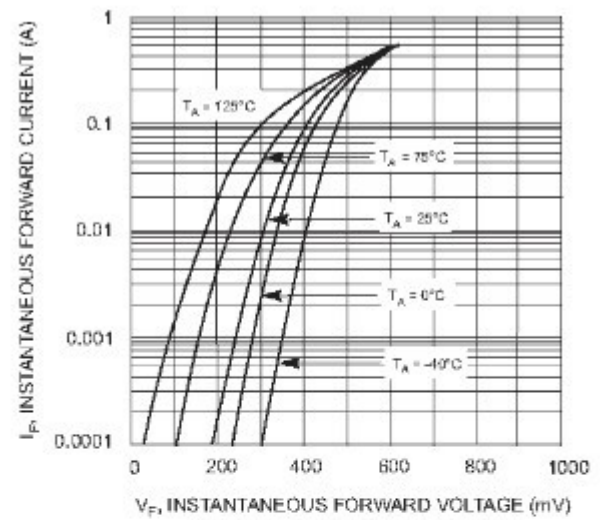


Fig. 2 Typical Forward Characteristics

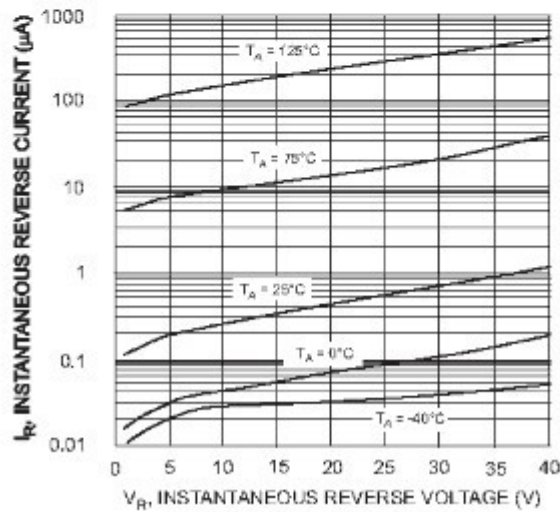


Fig. 3 Typical Reverse Characteristics

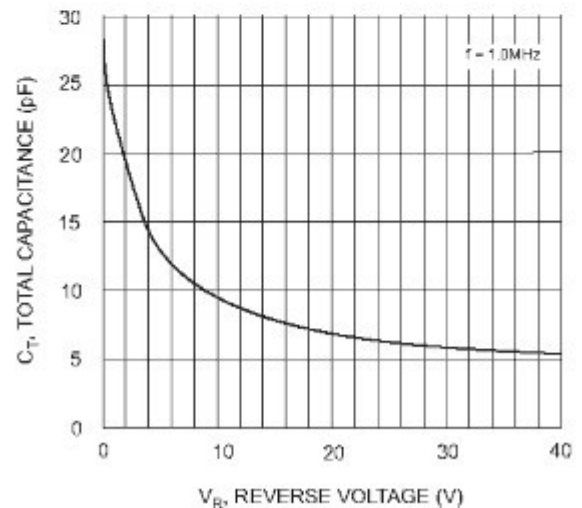
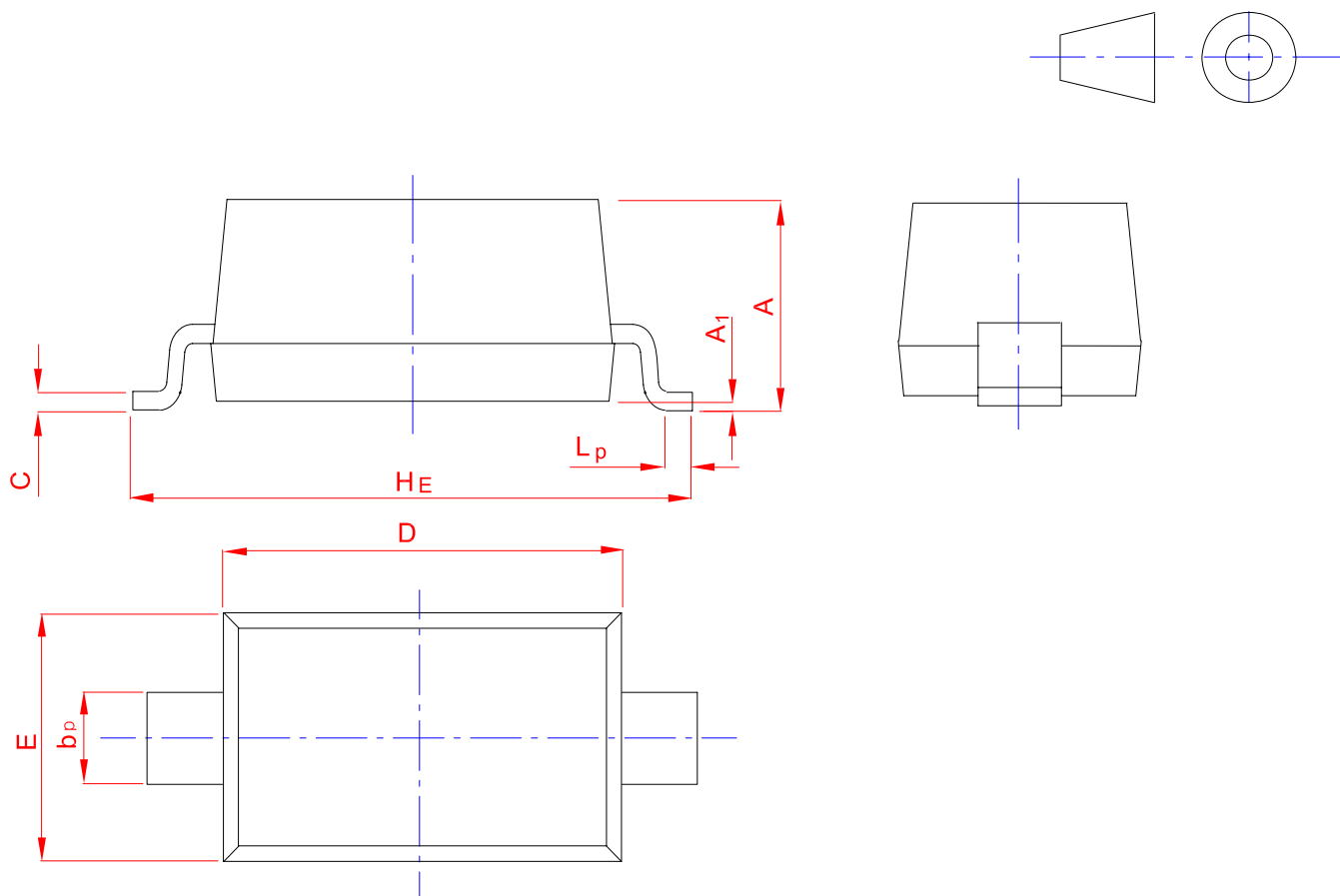


Fig. 4 Typ. Total Capacitance vs. Reverse Voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20